

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|---|---|------------------|---------|------------------|
| S1 | 276 | (si or silicon) near10 substrate and graded near10 (nitride or gan or algan) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/05 13:32 |
| S2 | 88 | (si or silicon) near10 substrate same graded near10 (nitride or gan or algan) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/05 13:45 |
| S3 | 10 | (si or silicon) near10 substrate same graded near10 (nitride or gan or algan) and weeks.in. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/05 13:47 |
| | | compress\$4 near2 stress\$4 same not temperature grad\$4 and "117"/\$4.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/12 13:30 |
| L2 | 24 | 1 and (si or silicon) near2 substrate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/12 13:31 |
| L3 | 112 | graded near5 (gan or algan or aluminum near2 nitride or gallium near2 nitride) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/12 14:10 |
| L1 | 56 | graded near2 (gan or algan or aluminum near2 nitride or gallium near2 nitride) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/12 14:10 |
| L4 | 92 | 3 and (silicon or si) not adj carbide near5 substrate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/12 14:11 |
| L8 | 6 | ("5387804" "5432808" "5393993").pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/12 14:38 |

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| L7 | 0 | ("5387804" "5432808" "5393993").pn. and grad\$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/12 14:38 |
| L6 | 8 | warren near2 weeks.in. and grad\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/12 14:39 |
| L5 | 72 | 3 and substrate near7 (silicon or si) not adj carbide | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/12 14:40 |
| L10 | 78 | buffer near5 (aln or aluminum near2 nitride) same (si or silicon) adj substrate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/12 15:01 |
| L12 | 1 | "20040213309" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/12 15:08 |
| L11 | 0 | "20040213309" and (si or silicon) near2 substrate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/12 15:08 |
| L13 | 2 | "20020020341".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/12 16:45 |
| L9 | 26 | substrate near5 (si or silicon) and vary\$4 near3 composit\$5 near10 (gan or gallium near2 nitride or aln or aluminum near2 nitride or algan) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/12 16:45 |
| L18 | 2 | "5923950".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/12 17:01 |
| L20 | 1 | (hugues near2 marchand or brendan near2 moran).in. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/12 17:33 |

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| L19 | 1 | "5923950".pn. and (silicon or si) adj substrate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/11/12 17:33 |
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